

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	10/711473	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/07 10:03
L2	0	(polysilicon near low near temperature near thin near film near transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/07 10:03
L3	243	(low near temperature near polysilicon near thin near film near transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/07 10:03
L4	0	(low near temperature near polysilicon near thin near film near transistor) and (buffer with between with gate with (insulating or dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/07 10:04
L5	1	(low near temperature near polysilicon near thin near film near transistor) and (buffer with gate with (insulating or dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/07 10:05
L6	1	(low near temperature near polysilicon near thin near film near transistor) and ((buffer adj layer) with (gate adj (insulating or dielectric)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/07 10:06
L7	1	(low near temperature near polysilicon near thin near film near transistor) and ((buffer) with (gate adj (insulating or dielectric)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/07 10:06
L8	0	(low near temperature near polysilicon near thin near film near transistor) and ((buffer) near10 (gate adj (insulating or dielectric)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/07 10:06
L9	216	(thin near film near transistor) and ((buffer) near10 (gate adj (insulating or dielectric)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/07 10:06

L10	157	(thin near film near transistor) and ((buffer adj layer) near10 (gate adj (insulating or dielectric)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/07 10:07
L11	16130	(thin near film near transistor) and ((buffer adj layer) near10 between (gate adj (insulating or dielectric)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/07 10:07
L12	20	(thin near film near transistor) and ((buffer adj layer) near10 between near10 (gate adj (insulating or dielectric)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/07 10:09
L13	9	(thin near film near transistor) and ((buffer adj layer) near10 between near10 (gate adj electrode) near10 (gate adj (insulating or dielectric)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/07 10:10